

## Small Signal Switching Diodes, High Voltage

- Features**

Silicon Epitaxial Planar Diodes  
Lead (Pb)-free component



- Applications**

General purposes



- Mechanical Data**

**Case:** MiniMELF Glass case (SOD80)

**Weight:** approx. 31 mg

**Cathode Band Color:** Black

- Absolute Maximum Ratings**

$T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified

Parameter	Test condition	Part	Symbol	Value	Unit
Repetitive peak reverse voltage		BAV100	$V_{RRM}$	60	V
		BAV101	$V_{RRM}$	120	V
		BAV102	$V_{RRM}$	200	V
		BAV103	$V_{RRM}$	250	V
Reverse voltage		BAV100	$V_R$	50	V
		BAV101	$V_R$	100	V
		BAV102	$V_R$	150	V
		BAV103	$V_R$	200	V
Peak forward surge current	$t_p = 1\text{ s}$		$I_{FSM}$	1	A
Repetitive peak forward current			$I_{FRM}$	625	mA
Forward continuous current			$I_F$	250	mA
Power dissipation			$P_{tot}$	500	mW

- Thermal Characteristics**

$T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Junction lead		$R_{thJL}$	350	K/W
Thermal resistance junction to ambient air	on PC board 50 mm x 50 mm x 1.6 mm	$R_{thJA}$	500	K/W
Junction temperature		$T_J$	175	$^{\circ}\text{C}$
Storage temperature range		$T_{stg}$	- 65 to + 175	$^{\circ}\text{C}$

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## ● Electrical Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified

Parameter	Test condition	Part	Symbol	Min	Typ.	Max	Unit
Forward voltage	$I_F = 100\text{ mA}$		$V_F$			1000	mV
Reverse current	$V_R = 50\text{ V}$	BAV100	$I_R$			100	nA
	$V_R = 100\text{ V}$	BAV101	$I_R$			100	nA
	$V_R = 150\text{ V}$	BAV102	$I_R$			100	nA
	$V_R = 200\text{ V}$	BAV103	$I_R$			100	nA
	$T_j = 100\text{ }^{\circ}\text{C}$ , $V_R = 50\text{ V}$	BAV100	$I_R$			15	$\mu\text{A}$
	$T_j = 100\text{ }^{\circ}\text{C}$ , $V_R = 100\text{ V}$	BAV101	$I_R$			15	$\mu\text{A}$
	$T_j = 100\text{ }^{\circ}\text{C}$ , $V_R = 150\text{ V}$	BAV102	$I_R$			15	$\mu\text{A}$
Breakdown voltage	$I_R = 100\text{ }\mu\text{A}$ , $t_p/T = 0.01$ , $t_p = 0.3\text{ ms}$	BAV100	$V_{(BR)}$	60			V
	$I_R = 100\text{ }\mu\text{A}$ , $t_p/T = 0.01$ , $t_p = 0.3\text{ ms}$	BAV101	$V_{(BR)}$	120			V
	$I_R = 100\text{ }\mu\text{A}$ , $t_p/T = 0.01$ , $t_p = 0.3\text{ ms}$	BAV102	$V_{(BR)}$	200			V
	$I_R = 100\text{ }\mu\text{A}$ , $t_p/T = 0.01$ , $t_p = 0.3\text{ ms}$	BAV103	$V_{(BR)}$	250			V
Diode capacitance	$V_R = 0$ , $f = 1\text{ MHz}$		$C_D$		1.5		pF
Differential forward resistance	$I_F = 10\text{ mA}$		$r_f$		5		$\Omega$
Reverse recovery time	$I_F = I_R = 30\text{ mA}$ , $i_R = 3\text{ mA}$ , $R_L = 100\text{ }\Omega$		$t_{rr}$			50	ns

## ● Typical Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified

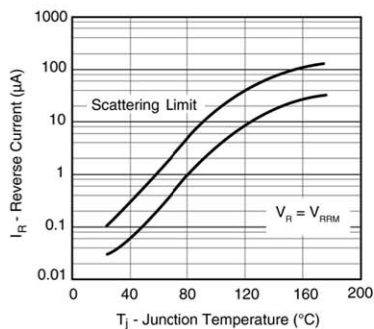


Figure 1. Reverse Current vs. Junction Temperature

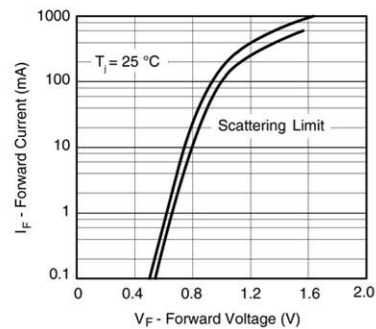


Figure 2. Forward Current vs. Forward Voltage

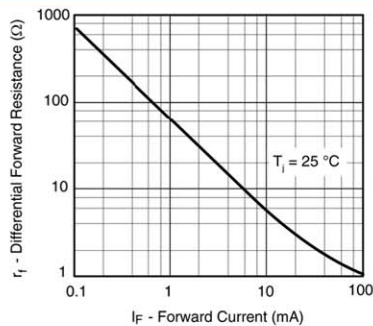


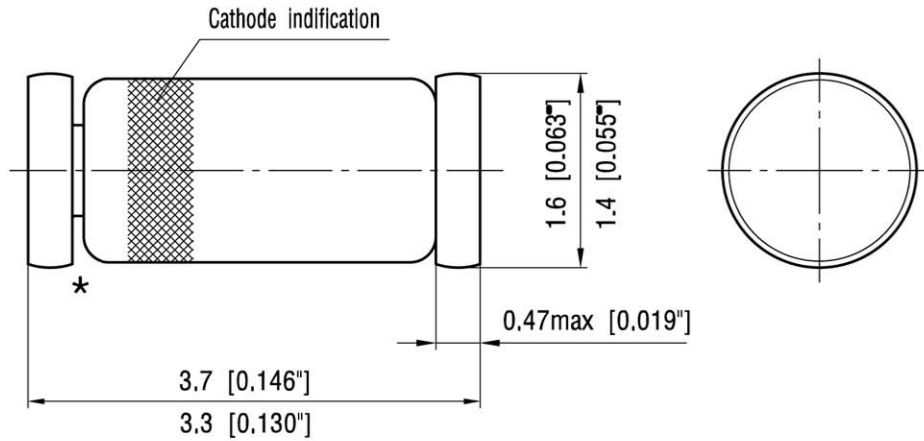
Figure 3. Differential Forward Resistance vs. Forward Current

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## Package Dimensions in millimeters (inches): SOD80



foot print recommendation:

